Fast Recovery Diodes (Hockey PUK Version), 920/1050 A

DO-200AB (B-PUK)

FEATURES

- High power fast recovery diode series
- 2.0 µs to 3.0 µs recovery time
- High voltage ratings up to 3000 V
- High current capability
- Optimized turn-on and turn-off characteristics
- Low forward recovery
- Fast and soft reverse recovery
- Press PUK encapsulation
- Case style conform to JEDEC® DO-200AB (B-PUK)
- Maximum junction temperature 150 °C
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

Pb-free RoHS COMPLIANT

TAPICAL APPLICATIONS

- Snubber diode for GTO
- High voltage freewheeling diode
- Fast recovery rectifier applications

PRODUCT SUMMARY	
$I_{F(AV)}$	920 A to 1050 A
Package	DO-200AB (B-PUK)
Circuit configuration	Single Diode

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	TEST CONDITIONS	SD1053C..L		UNITS
		S20	S30	
$I_{F(AV)}$		1050	920	A
	T_{hs}	55	55	°C
$I_{F(RMS)}$		1940	1700	A
I_{FSM}	50 Hz	15 000	13 000	
	60 Hz	15 700	13 610	
V_{RRM}	Range	1800 to 2500	1800 to 3000	V
t_{rr}		2.0	3.0	µs
	T_J	25		°C
T_J		-40 to 150		

ELECTRICAL SPECIFICATIONS

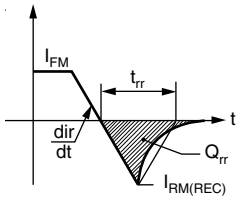
VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{RRM}, MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM}, MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-SD1053C..S20L	18	1800	1900	50
	22	2200	2300	
	25	2500	2600	
VS-SD1053C..S30L	18	1800	1900	
	22	2200	2300	
	25	2500	2600	
	28	2800	2900	
	30	3000	3100	

FORWARD CONDUCTION

PARAMETER	SYMBOL	TEST CONDITIONS			SD1053C..L S20	SD1053C..L S30	UNITS
Maximum average forward current at heatsink temperature	$I_{F(AV)}$	180° conduction, half sine wave			1050 (450)	920 (390)	A
		Double side (single side) cooled			55 (85)	55 (85)	°C
Maximum RMS forward current	$I_{F(RMS)}$	25 °C heatsink temperature double side cooled			1940	1700	A
Maximum peak, one-cycle forward, non-repetitive surge current	I_{FSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	15 000	13 000	
		t = 8.3 ms			15 700	13 610	
		t = 10 ms	100 % V_{RRM} reapplied		12 620	10 930	
		t = 8.3 ms			13 210	11 450	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		1125	845	kA^2s
		t = 8.3 ms			1027	772	
		t = 10 ms	100 % V_{RRM} reapplied		796	598	
		t = 8.3 ms			727	546	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied			11 250	8450	$kA^2\sqrt{s}$
Low level value of threshold voltage	$V_{F(TO)1}$	(16.7 % x π x $I_{F(AV)}$ < I < π x $I_{F(AV)}$), $T_J = T_J$ maximum			1.34	1.51	V
High level value of threshold voltage	$V_{F(TO)2}$	(I > π x $I_{F(AV)}$), $T_J = T_J$ maximum			1.48	1.67	
Low level value of forward slope resistance	r_{f1}	(16.7 % x π x $I_{F(AV)}$ < I < π x $I_{F(AV)}$), $T_J = T_J$ maximum			0.37	0.50	mΩ
High level value of forward slope resistance	r_{f2}	(I > π x $I_{F(AV)}$), $T_J = T_J$ maximum			0.33	0.45	
Maximum forward voltage drop	V_{FM}	I_{pk} = 1500 A, $T_J = T_J$ maximum, t_p = 10 ms sinusoidal wave			1.90	2.26	V

RECOVERY CHARACTERISTICS

CODE	MAXIMUM VALUE AT T_J = 25 °C	TEST CONDITIONS			TYPICAL VALUES AT T_J = 150 °C		
	t_{rr} AT 25 % I_{RRM} (µs)	I_{pk} SQUARE PULSE (A)	dI/dt (A/µs)	V_r (V)	t_{rr} AT 25 % I_{RRM} (µs)	Q_{rr} (µC)	I_{rr} (A)
S20	2.0	1000	100	- 50	4.0	400	180
S30	3.0				4.5	550	230



THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating and storage temperature range	T_J, T_{Stg}		-40 to 150	°C
Maximum thermal resistance, case junction to heatsink	R_{thJ-hs}	DC operation single side cooled	0.073	K/W
		DC operation double side cooled	0.031	
Mounting force, ± 10 %			14 700 (1500)	N (kg)
Approximate weight			255	g
Case style		See dimensions - link at the end of datasheet	DO-200AB (B-PUK)	

ΔR_{thJ-hs} CONDUCTION

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.009	0.008	0.006	0.006	$T_J = T_J$ maximum	K/W
120°	0.011	0.011	0.011	0.011		
90°	0.014	0.014	0.015	0.015		
60°	0.020	0.021	0.021	0.022		
30°	0.036	0.036	0.036	0.036		

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

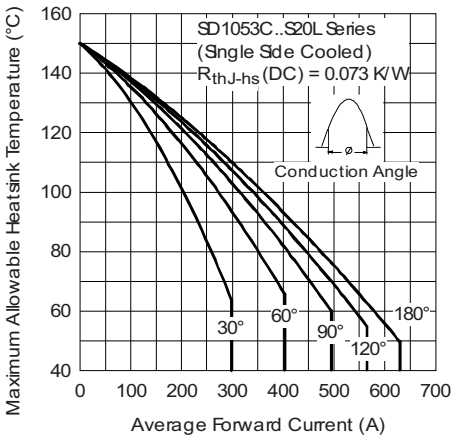


Fig. 1 - Current Ratings Characteristics

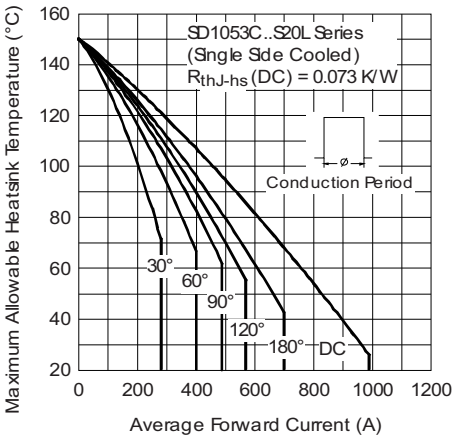


Fig. 2 - Current Ratings Characteristics

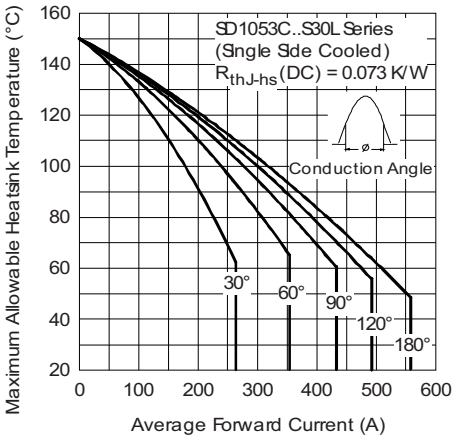


Fig. 3 - Current Ratings Characteristics

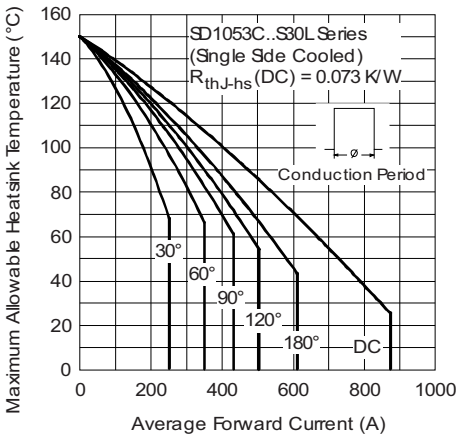


Fig. 4 - Current Ratings Characteristics

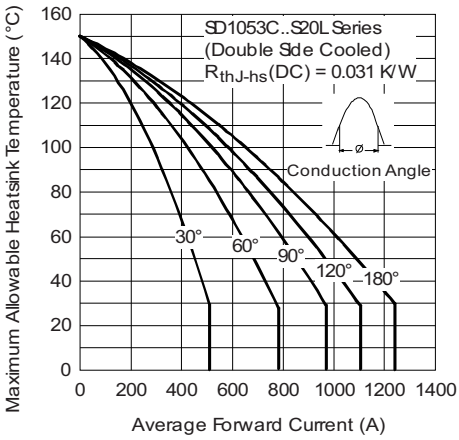


Fig. 5 - Current Ratings Characteristics

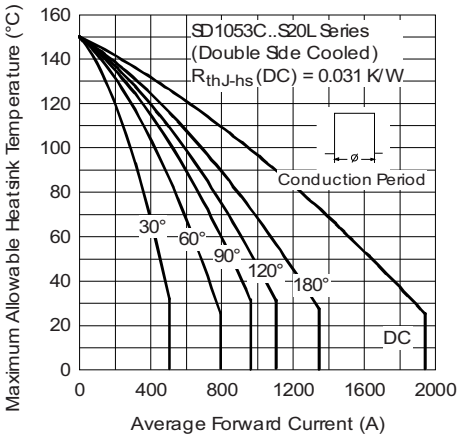


Fig. 6 - Current Ratings Characteristics

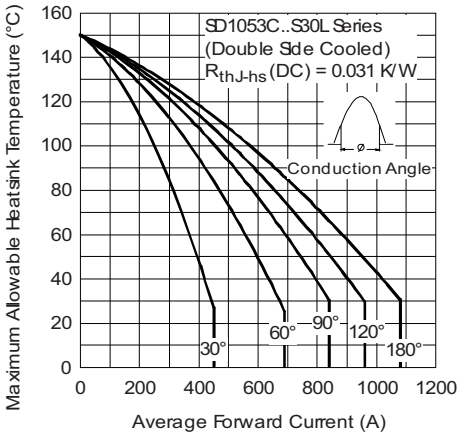


Fig. 7 - Current Ratings Characteristics

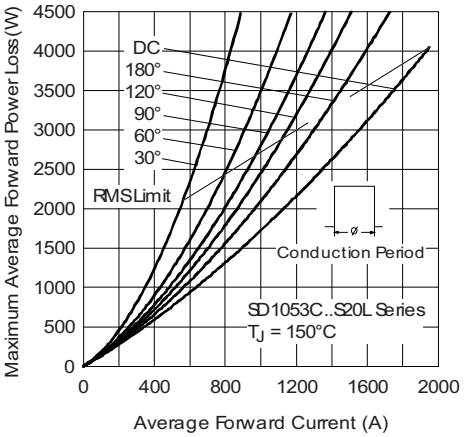


Fig. 10 - Forward Power Loss Characteristics

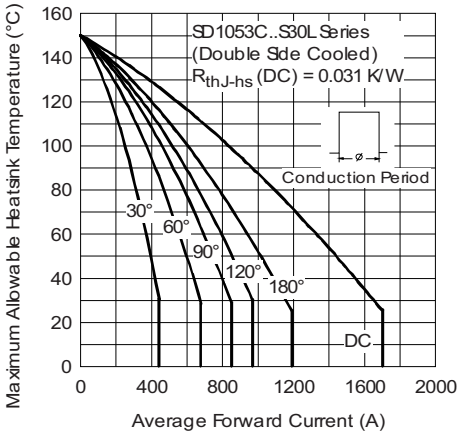


Fig. 8 - Current Ratings Characteristics

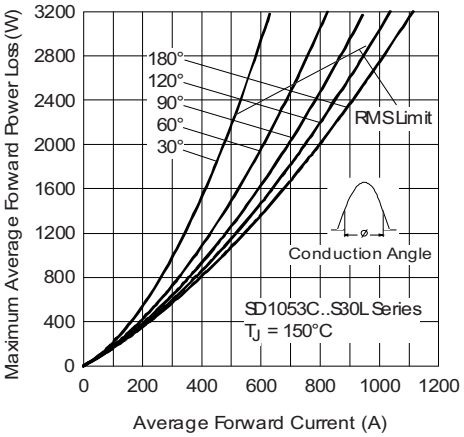


Fig. 11 - Forward Power Loss Characteristics

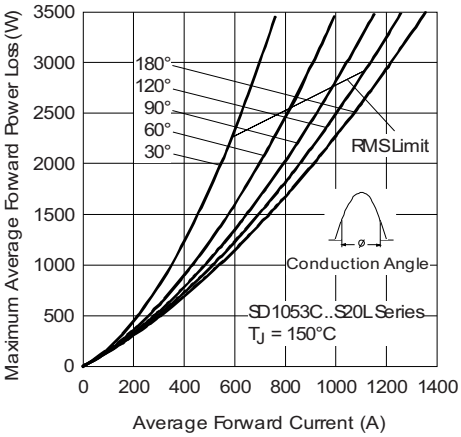


Fig. 9 - Forward Power Loss Characteristics

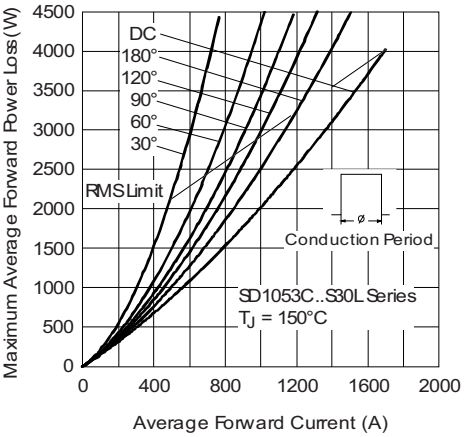


Fig. 12 - Forward Power Loss Characteristics

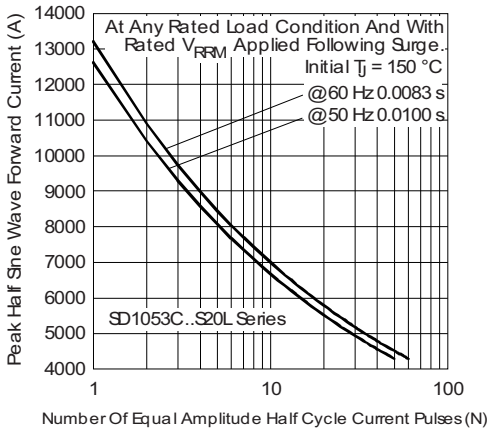


Fig. 13 - Maximum Non-Repetitive Surge Current

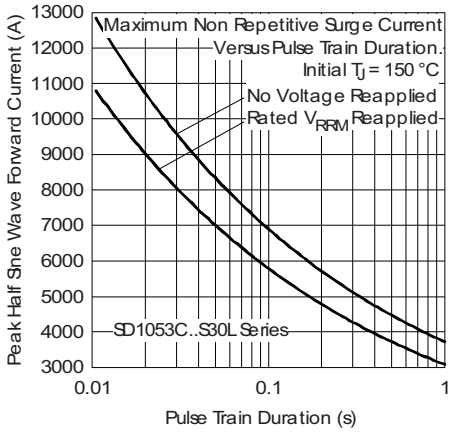


Fig. 16 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

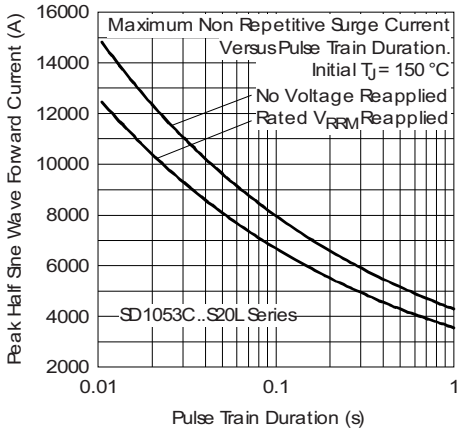


Fig. 14 - Maximum Non-Repetitive Surge Current

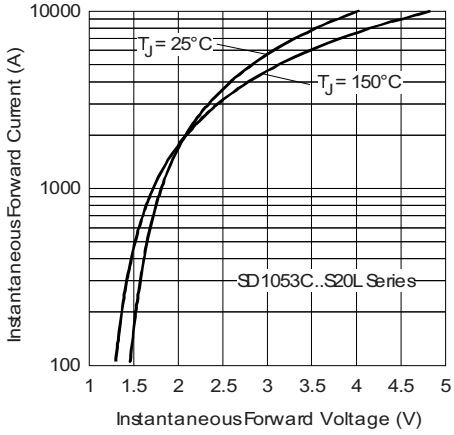


Fig. 17 - Forward Voltage Drop Characteristics

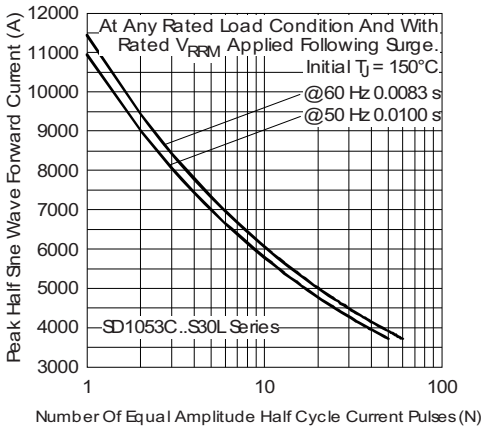


Fig. 15 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

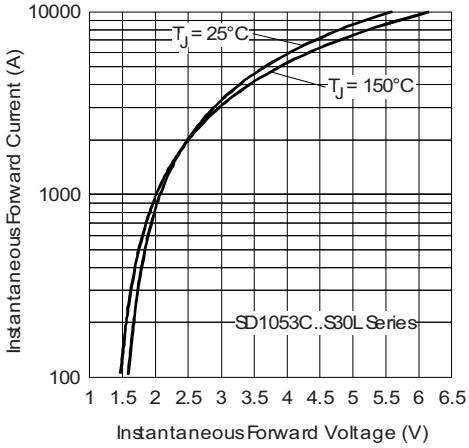


Fig. 18 - Forward Voltage Drop Characteristics

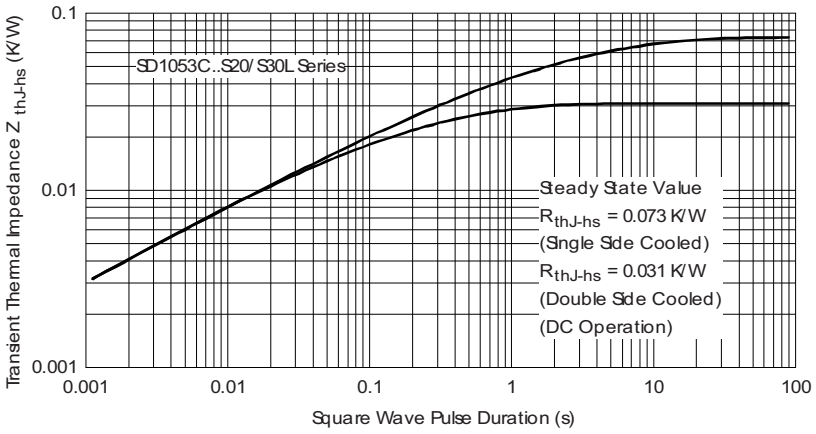


Fig. 19 - Thermal Impedance Z_{thJ-hs} Characteristic

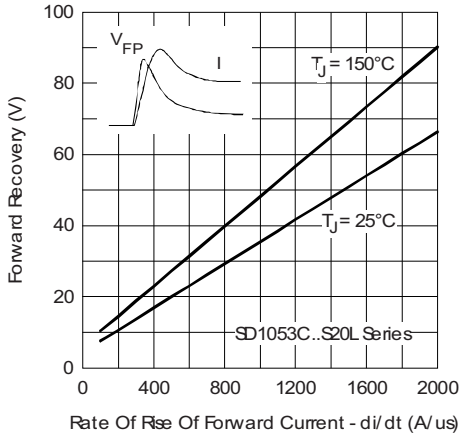


Fig. 20 - Typical Forward Recovery Characteristics

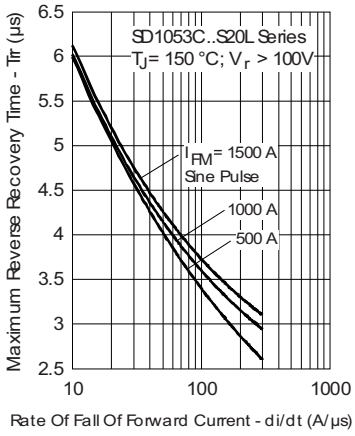


Fig. 22 - Recovery Time Characteristics

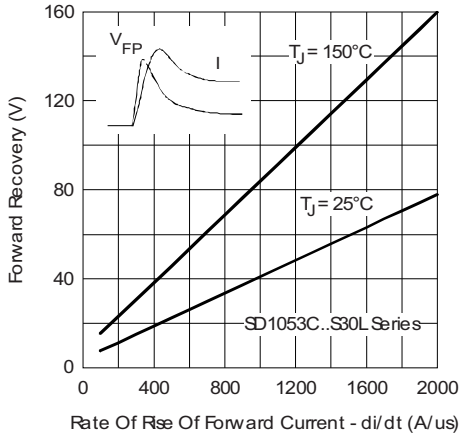


Fig. 21 - Typical Forward Recovery Characteristics

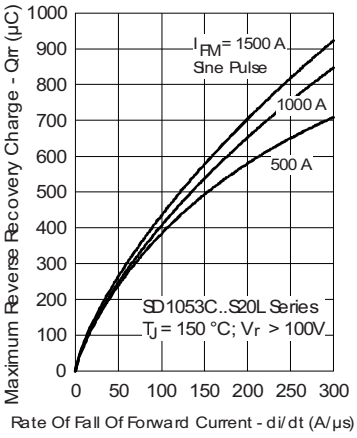


Fig. 23 - Recovery Charge Characteristics

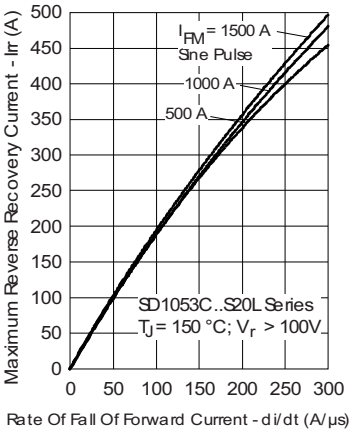


Fig. 24 - Recovery Current Characteristics

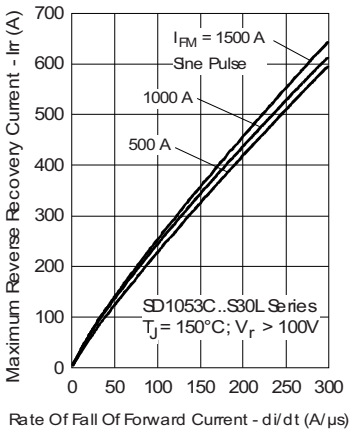


Fig. 27 - Recovery Current Characteristics

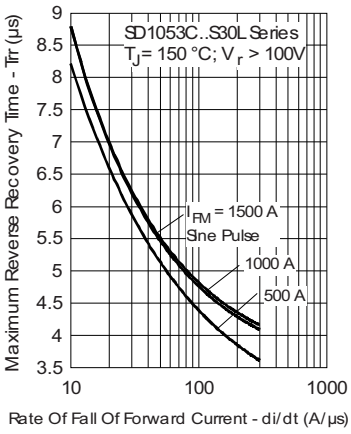


Fig. 25 - Recovery Time Characteristics

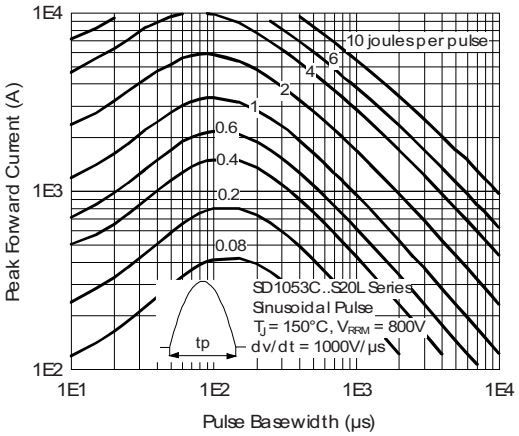


Fig. 28 - Maximum Total Energy Loss Per Pulse Characteristics

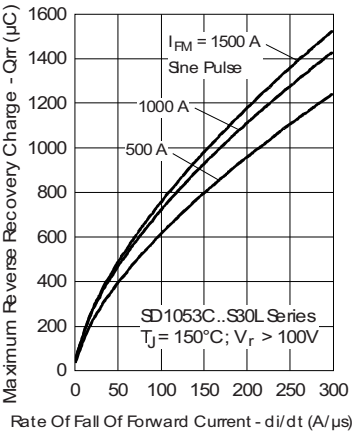


Fig. 26 - Recovery Charge Characteristics

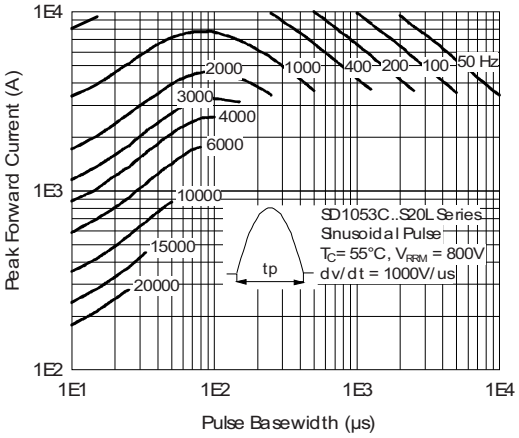


Fig. 29 - Frequency Characteristics

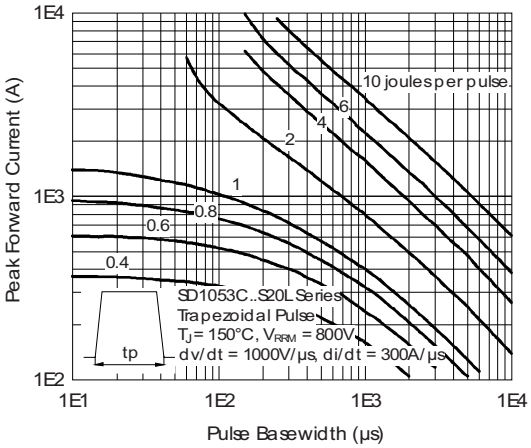


Fig. 30 - Maximum Total Energy Loss Per Pulse Characteristics

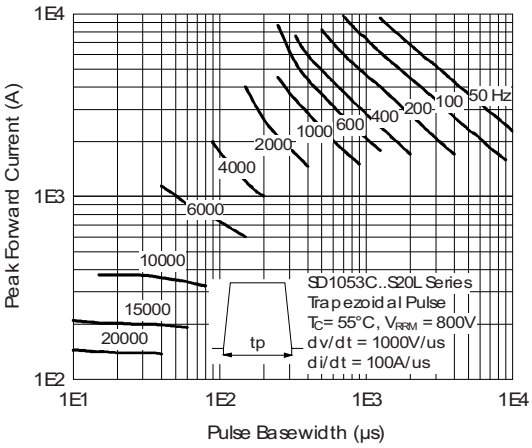


Fig. 33 - Frequency Characteristics

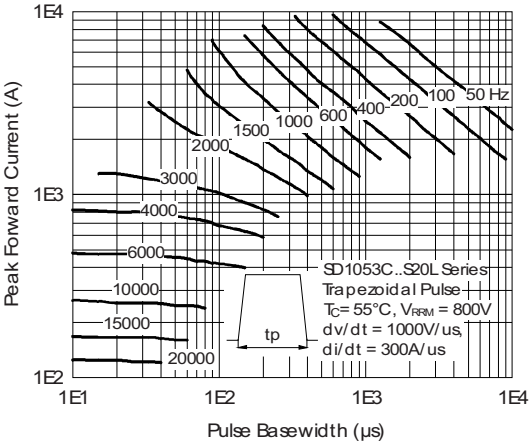


Fig. 31 - Frequency Characteristics

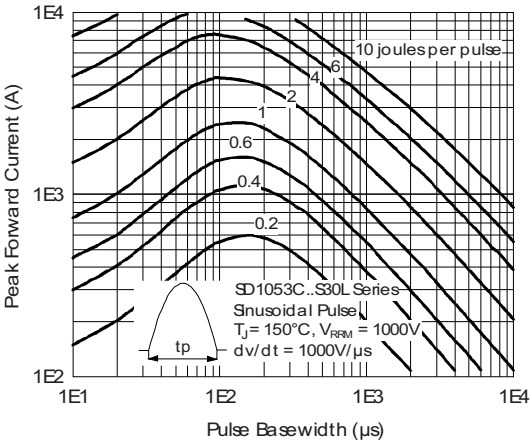


Fig. 34 - Maximum Total Energy Loss Per Pulse Characteristics

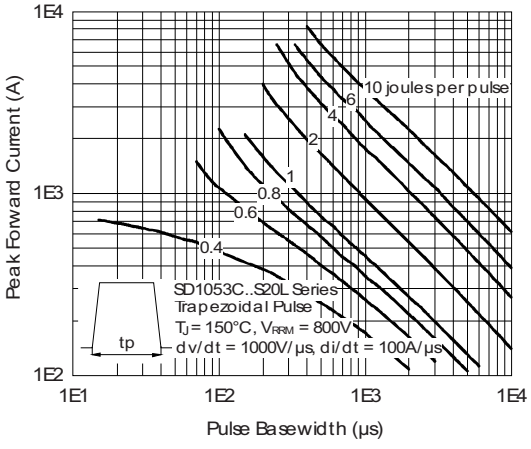


Fig. 32 - Maximum Total Energy Loss Per Pulse Characteristics

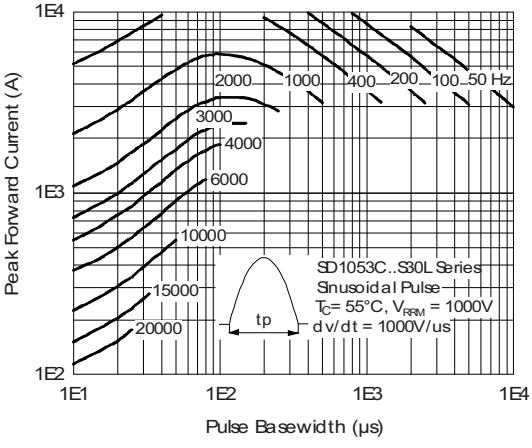


Fig. 35 - Frequency Characteristics

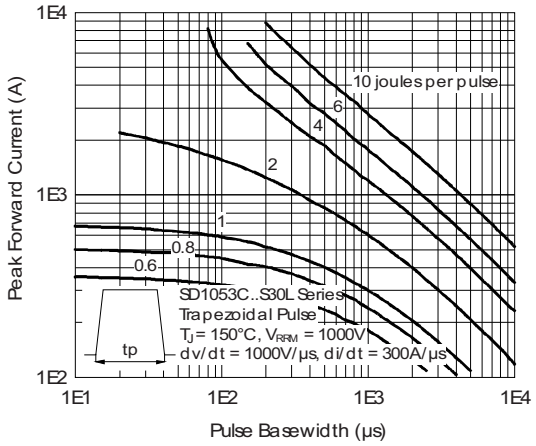


Fig. 36 - Maximum Total Energy Loss Per Pulse Characteristics

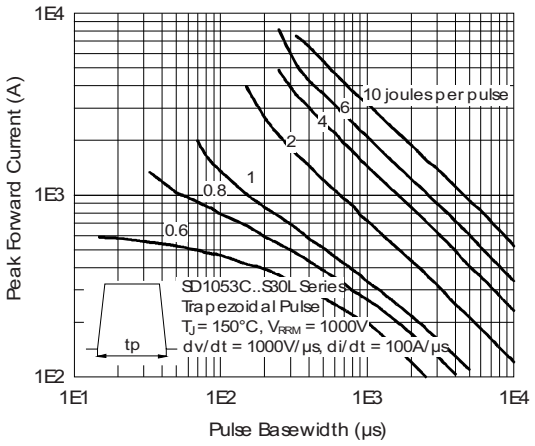


Fig. 38 - Maximum Total Energy Loss Per Pulse Characteristics

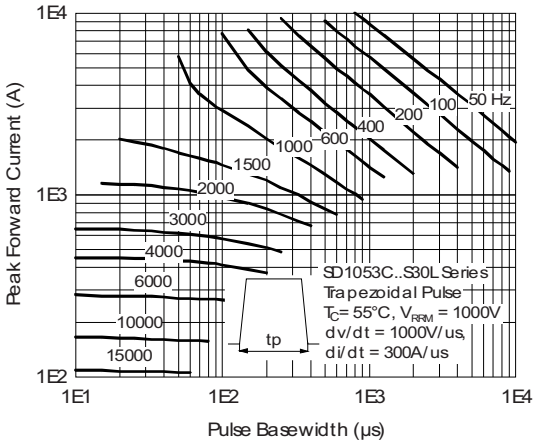


Fig. 37 - Frequency Characteristics

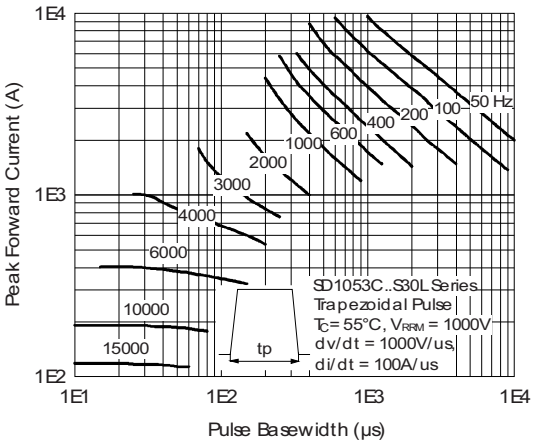


Fig. 39 - Frequency Characteristics

ORDERING INFORMATION TABLE

Device code

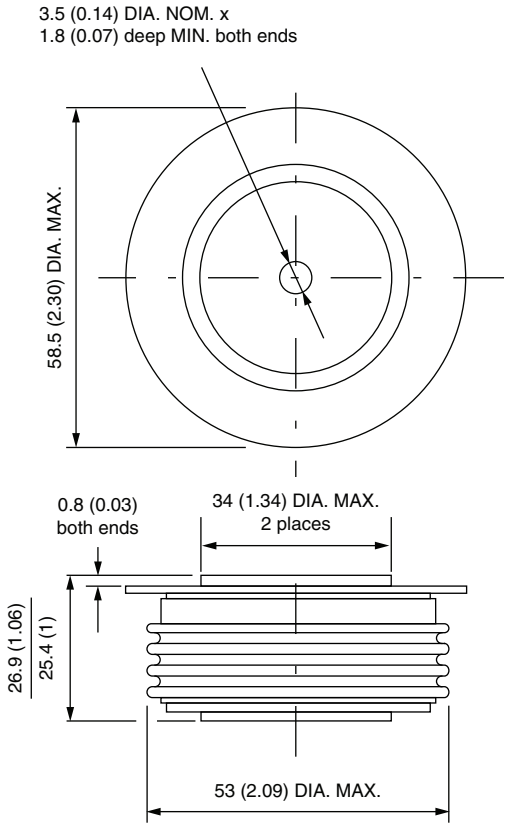
VS-	SD	105	3	C	30	S30	L
1	2	3	4	5	6	7	8

- **1** - Vishay Semiconductors product
- **2** - Diode
- **3** - Essential part number
- **4** - 3 = Fast recovery
- **5** - C = Ceramic PUK
- **6** - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- **7** - t_{rr} code
- **8** - L = PUK case DO-200AB (B-PUK)

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95246

DO-200AB (B-PUK)

DIMENSIONS in millimeters (inches)



Quote between upper and lower pole pieces has to be considered after application of mounting force (see Thermal and Mechanical Specifications)

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Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9